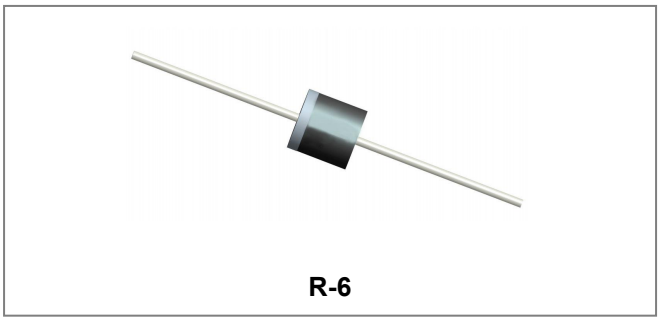
Technical Data
Data Sheet N0450, Rev. B

RoHS

FR601 THRU FR607
FAST RECOVERY RECTIFIERS



R-6

Features

- Diffused Junction
- Low Forward Voltage Drop
- High Current Capability
- High Reliability
- High Surge Current Capability
- This is a Pb − Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Circuit Diagram

Mechanical Data

- Case: R-6 molded plastic
- Terminals: Plated axial leads, solderable per MIL-STD-202, Method 208
- Polarity: Color band denotes cathode end
- Mounting Position: Any
- Weight: 2.1 grams

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

Single phase half-wave 60Hz, resistive or inductive load, for capacitive load current derate by 20%.

Characteristic	Symbol	FR 601	FR 602	FR 603	FR 604	FR 605	FR 606	FR 607	Units
Maximum repetitive peak reverse voltage Maximum DC blocking voltage	V_{RRM} V_{DC}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum average forward rectified current 0.375"(9.5mm) lead length at @T_A =55°C	$I_{(AV)}$	6.0							A
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	I_{FSM}	200							A
Maximum instantaneous forward voltage at 6.0A	V_F	1.2							V
Maximum DC reverse current @T_A = 25°C At Rated DC Blocking Voltage @T_A = 100°C	I_{RM}	10 200							μA
Maximum reverse recovery time (Note 1)	t_{rr}	150				250	500		ns
Typical Junction Capacitance (Note 2)	C_J	100							pF
Operating junction temperature range	T_J	-65 to +125							°C
Operating storage temperature range	T_{STG}	-65 to +150							°C

***Glass passivated forms are available upon request**

Note: 1. Reverse recovery condition IF=0.5A, IR=1.0A, Irr=0.25A
2. Measured at 1MHz and applied reverse voltage of 4.0V D.C.

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Ratings and Characteristics Curves

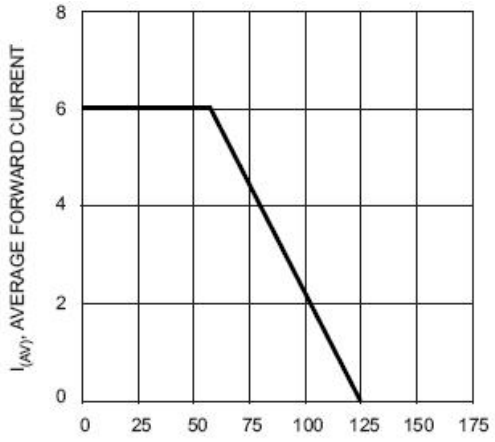


Fig. 1, Typical Forward Current Derating Curve

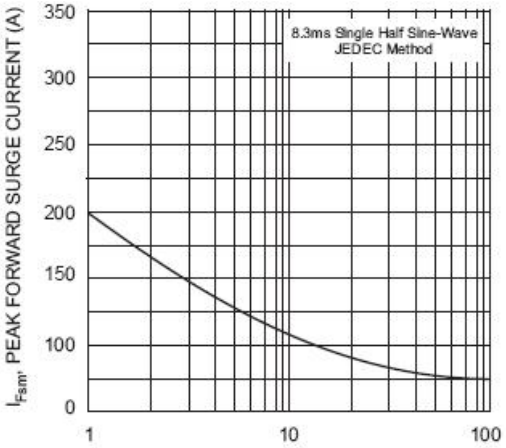


Fig. 2 Max Non-Repetitive Peak Surge Current

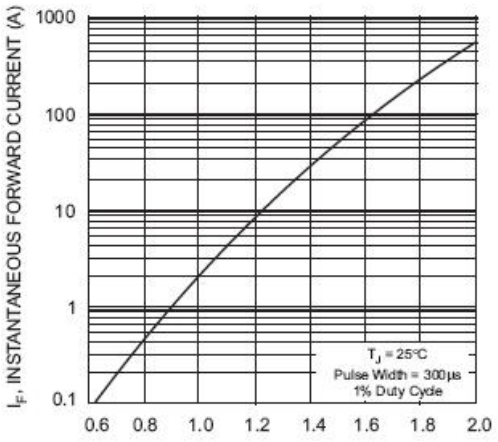


Fig. 3, Typical Instantaneous Forward Characteristics

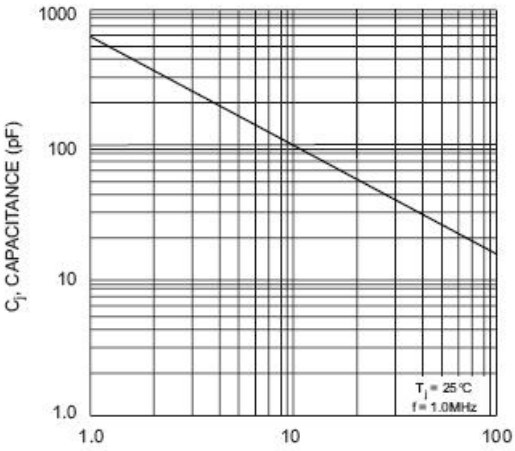
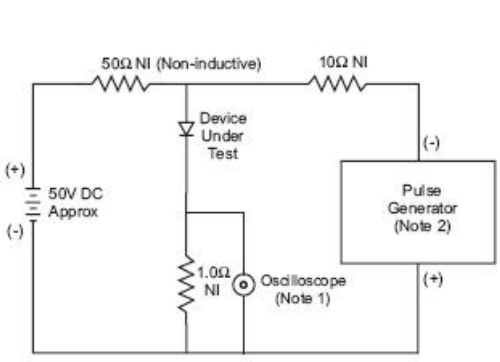


Fig. 4 Typical Junction Capacitance



Notes:
1. Rise Time = 7.0ns max. Input Impedance = 1.0MΩ, 22pF.
2. Rise Time = 10ns max. Input Impedance = 50Ω.

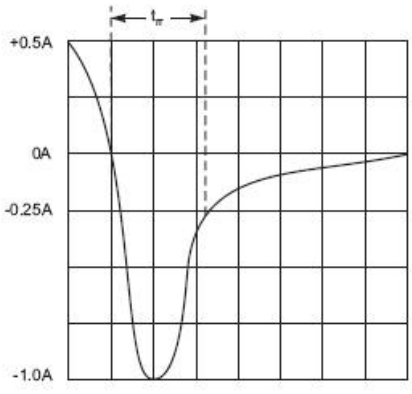


Fig. 5 Reverse Recovery Time Characteristic and Test Circuit

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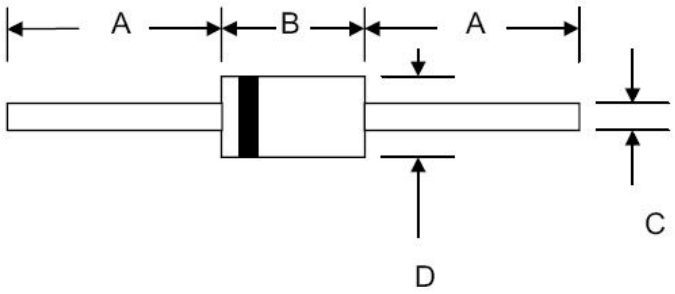
Mechanical Dimensions R-6



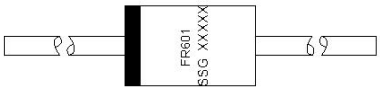
SYMBOL	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	25.4	-	1.000	-
B	8.60	9.10	0.340	0.360
C	1.2	1.3	0.048	0.052
D	8.60	9.10	0.340	0.360

Ordering Information

Device	Package	Shipping
FR601-FR607	R-6 (Pb-Free)	500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram

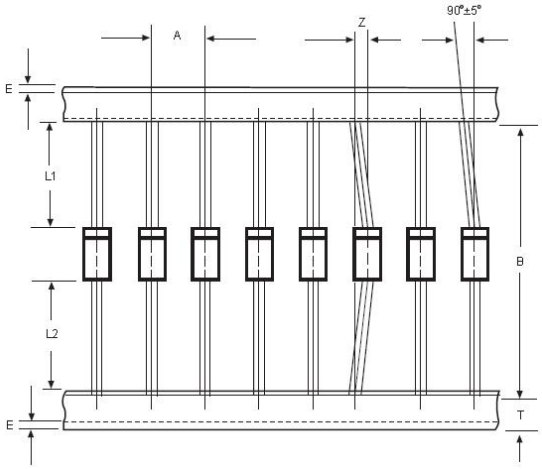


Where XXXXX is YYWWL

FR601 = Part Name
SSG = SSG
YY = Year
WW = Week
L = Lot Number

Cautions: Molding resin
Epoxy resin UL:94V-0

Carrier Tape Specification R-6



SYMBOL	Millimeters	
	Min.	Max.
A	9.50	10.50
B	50.9	53.9
Z	-	1.20
T	5.60	6.40
E	-	0.80
IL1-L2I	-	1.0

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